NTMFD4902NF

Dual N-Channel Power MOSFET with Integrated Schottky

30 V, High Side 18 A / Low Side 23 A, Dual N−Channel SO8FL

ON Semiconductor®

http://onsemi.com

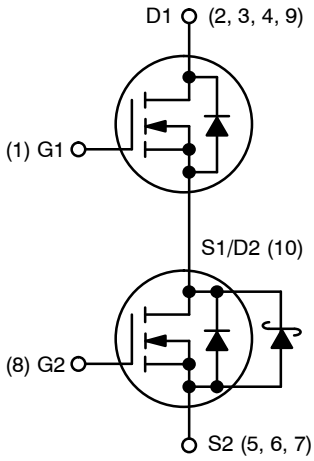
$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D MAX
Q1 Top FET 30 V	6.5 mΩ @ 10 V	18 A
	10 mΩ @ 4.5 V	
Q2 Bottom FET 30 V	4.1 mΩ @ 10 V	23 A
	6.2 mΩ @ 4.5 V	

Features

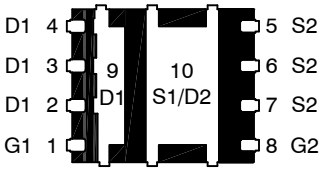
- Co−Packaged Power Stage Solution to Minimize Board Space
- Low Side MOSFET with Integrated Schottky
- Minimized Parasitic Inductances
- Optimized Devices to Reduce Power Losses
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- DC−DC Converters
- System Voltage Rails
- Point of Load

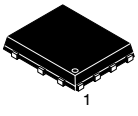


PIN CONNECTIONS



(Bottom View)

MARKING DIAGRAM



DFN8
CASE 506BX

4902NF	= Specific Device Code
A	= Assembly Location
Y	= Year
W	= Work Week
ZZ	= Lot Traceability

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS (T_J = 25°C unless otherwise stated)

Parameter				Symbol	Value	Unit
Drain−to−Source Voltage			Q1	V_{DSS}	30	V
Drain−to−Source Voltage			Q2			
Gate−to−Source Voltage			Q1	V_{GS}	±20	V
Gate−to−Source Voltage			Q2			
Continuous Drain Current $R_{\theta JA}$ (Note 1)	Steady State	T_A = 25°C	Q1	I_D	13.5	A
		T_A = 85°C			9.7	
		T_A = 25°C	Q2		17.5	
		T_A = 85°C			12.6	
Power Dissipation RθJA (Note 1)		T_A = 25°C	Q1	P_D	1.90	W
			Q2		1.99	
Continuous Drain Current $R_{\theta JA} \le$ 10 s (Note 1)		T_A = 25°C	Q1	I_D	18.2	A
		T_A = 85°C			13.1	
		T_A = 25°C	Q2		23	
		T_A = 85°C			16.6	
Power Dissipation $R_{\theta JA} \le$ 10 s (Note 1)		T_A = 25°C	Q1	P_D	3.45	W
			Q2		3.45	
Continuous Drain Current $R_{\theta JA}$ (Note 2)		T_A = 25°C	Q1	I_D	10.3	A
		T_A = 85°C			7.4	
		T_A = 25°C	Q2		13.3	
		T_A = 85°C			9.6	
Power Dissipation $R_{\theta JA}$ (Note 2)		T_A = 25 °C	Q1	P_D	1.10	W
			Q2		1.16	
Pulsed Drain Current		TA = 25°C tp = 10 μs	Q1	I_{DM}	60	A
			Q2		80	
Operating Junction and Storage Temperature			Q1	T_J, T_{STG}	−55 to +150	°C
			Q2			
Source Current (Body Diode)			Q1	I_S	3.4	A
			Q2		4.9	
Drain to Source dV/dt				dV/dt	6.0	V/ns
Single Pulse Drain−to−Source Avalanche Energy (T_J = 25C, V_{DD} = 50 V, V_{GS} = 10 V, I_L = XX A_{pk}, L = 0.1 mH, R_G = 25 Ω)		24 A	Q1	EAS	28.8	mJ
		27 A	Q2	EAS	36.5	
Lead Temperature for Soldering Purposes (1/8” from case for 10 s)				T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface−mounted on FR4 board using 1 sq−in pad, 2 oz Cu.
2. Surface−mounted on FR4 board using the minimum recommended pad size of 100 mm^2.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	FET	Symbol	Value	Unit
Junction−to−Ambient − Steady State (Note 3)	Q1	$R_{\theta JA}$	65.9	°C/W
	Q2		62.8	
Junction−to−Ambient − Steady State (Note 4)	Q1	$R_{\theta JA}$	113.2	
	Q2		108	
Junction−to−Ambient − (t ≤ 10 s) (Note 3)	Q1	$R_{\theta JA}$	36.2	
	Q2		36.2	

3. Surface−mounted on FR4 board using 1 sq−in pad, 2 oz Cu.
4. Surface−mounted on FR4 board using the minimum recommended pad size of 100 mm^2.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	FET	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS								
Drain−to−Source Breakdown Voltage	Q1	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 250 μA		30			V
	Q2		V_{GS} = 0 V, I_D = 1.0 mA		30			
Drain−to−Source Breakdown Voltage Temperature Coefficient	Q1	$V_{(BR)DSS}$ / T_J				18		mV / °C
	Q2					15		
Zero Gate Voltage Drain Current	Q1	I_{DSS}	V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			1	μA
				T_J = 125°C			10	
	Q2		V_{GS} = 0 V, V_{DS} = 24 V	T_J = 25°C			500	
Gate−to−Source Leakage Current	Q1	I_{GSS}	V_{GS} = 0 V, VDS = ±20 V				±100	nA
	Q2						±100	
ON CHARACTERISTICS (Note 5)								
Gate Threshold Voltage	Q1	$V_{GS(TH)}$	V_{GS} = VDS, I_D = 250 μA		1.2		2.2	V
	Q2				1.2		2.2	
Negative Threshold Temperature Coefficient	Q1	$V_{GS(TH)}$ / T_J				4.5		mV / °C
	Q2					4.0		
Drain−to−Source On Resistance	Q1	$R_{DS(on)}$	V_{GS} = 10 V	I_D = 10 A		5.2	6.5	mΩ
			V_{GS} = 4.5 V	I_D = 10 A		8.0	10	
	Q2		V_{GS} = 10 V	I_D = 15 A		3.3	4.1	
			V_{GS} = 4.5 V	I_D = 15 A		5.0	6.2	
Forward Transconductance	Q1	g_{FS}	V_{DS} = 1.5 V, I_D = 10 A			28		S
	Q2					35		
CHARGES, CAPACITANCES & GATE RESISTANCE								
Input Capacitance	Q1	C_{ISS}	V_{GS} = 0 V, f = 1 MHz, V_{DS} = 15 V			1150		pF
	Q2					1590		
Output Capacitance	Q1	C_{OSS}				360		
	Q2					813		
Reverse Capacitance	Q1	C_{RSS}				105		
	Q2					83		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
CHARGES, CAPACITANCES & GATE RESISTANCE							
Total Gate Charge	Q1	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 15 V; I_D = 10 A		9.7		nC
	Q2				11.5		
Threshold Gate Charge	Q1	$Q_{G(TH)}$			1.1		
	Q2				1.4		
Gate−to−Source Charge	Q1	Q_{GS}			3.3		
	Q2				4.2		
Gate−to−Drain Charge	Q1	Q_{GD}			3.7		
	Q2				3.4		
Total Gate Charge	Q1	$Q_{G(TOT)}$	V_{GS} = 10 V, V_{DS} = 15 V; I_D = 10 A		19.1		nC
	Q2				24.9		
SWITCHING CHARACTERISTICS (Note 6)							
Turn−On Delay Time	Q1	$t_{d(ON)}$	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 10 A, R_G = 3.0 Ω		9.0		ns
	Q2				10.5		
Rise Time	Q1	t_r			15		
	Q2				15.2		
Turn−Off Delay Time	Q1	$t_{d(OFF)}$			14		
	Q2				17.7		
Fall Time	Q1	t_f			4.0		
	Q2				4.7		
SWITCHING CHARACTERISTICS (Note 6)							
Turn−On Delay Time	Q1	$t_{d(ON)}$	V_{GS} = 10 V, V_{DS} = 15 V, I_D = 10 A, R_G = 3.0 Ω		6.0		ns
	Q2				7.0		
Rise Time	Q1	t_r			14		
	Q2				14		
Turn−Off Delay Time	Q1	$t_{d(OFF)}$			17		
	Q2				22		
Fall Time	Q1	t_f			3.0		
	Q2				3.3		
DRAIN−SOURCE DIODE CHARACTERISTICS							
Forward Voltage	Q1	V_{SD}	V_{GS} = 0 V, I_S = 3 A	T_J = 25°C	0.75	1.0	V
				T_J = 125°C	0.62		
	Q2		V_{GS} = 0 V, I_S = 2 A	T_J = 25°C	0.37	0.70	
				T_J = 125°C	0.31		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	FET	Symbol	Test Condition	Min	Typ	Max	Unit
DRAIN−SOURCE DIODE CHARACTERISTICS							
Reverse Recovery Time	Q1	t_{RR}	V_{GS} = 0 V, d_{IS}/d_t = 100 A/μs, I_S = 3 A		23		ns
	Q2				24.5		
Charge Time	Q1	ta			12		
	Q2				13		
Discharge Time	Q1	tb			11		
	Q2				11.5		
Reverse Recovery Charge	Q1	Q_{RR}			12		nC
	Q2				24		
PACKAGE PARASITIC VALUES							
Source Inductance	Q1	L_S	T_A = 25°C		0.38		nH
	Q2				0.65		
Drain Inductance	Q1	L_D			0.054		nH
	Q2				0.007		
Gate Inductance	Q1	L_G			1.5		nH
	Q2				1.5		
Gate Resistance	Q1	R_G			0.8		Ω
	Q2				0.8		

5. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.
6. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Device	Package	Shipping†
NTMFD4902NFT1G	DFN8 (Pb−Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS – Q1

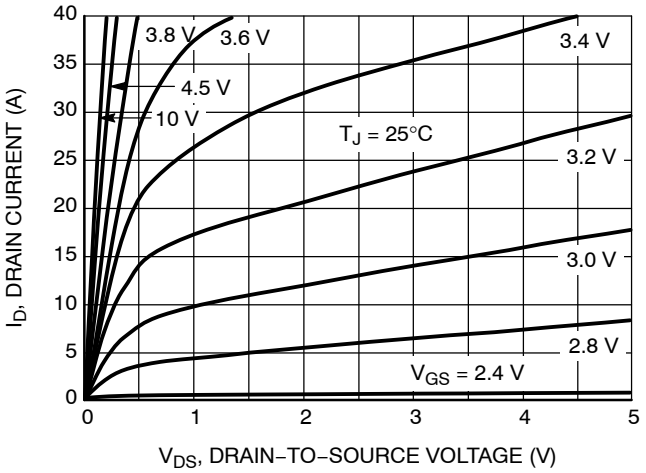


Figure 1. On−Region Characteristics

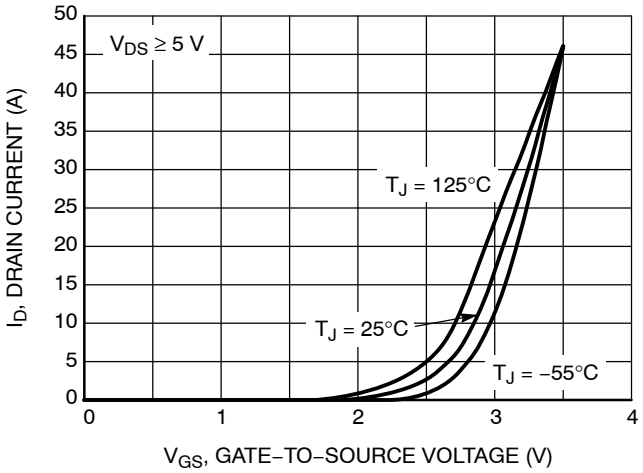


Figure 2. Transfer Characteristics

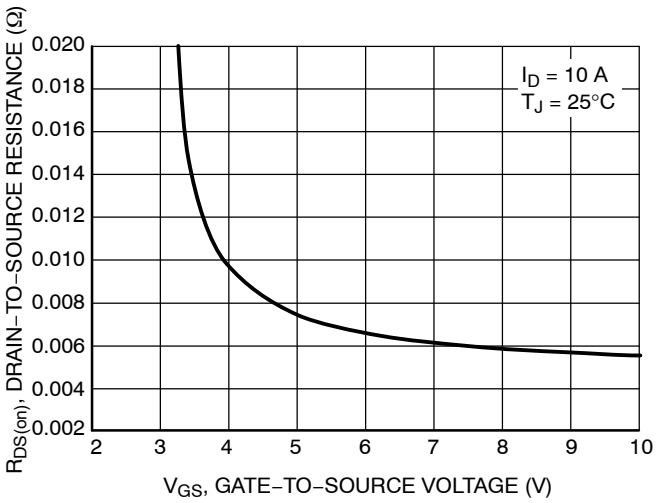


Figure 3. On−Resistance vs. Gate−to−Source Resistance

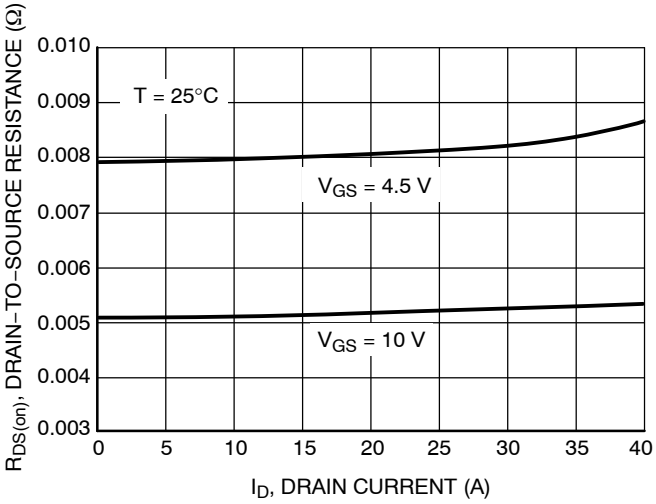


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

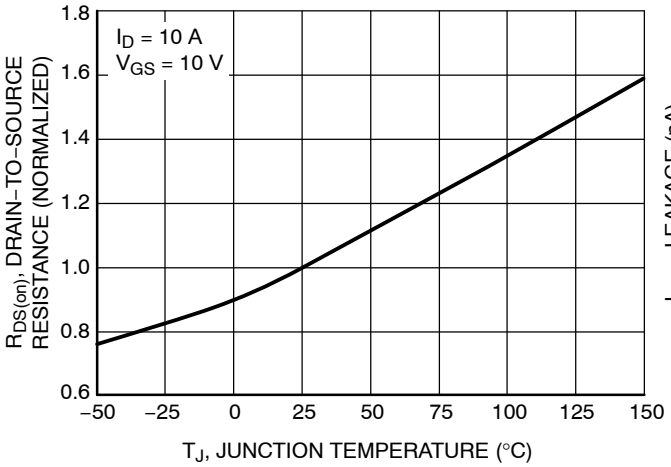


Figure 5. On−Resistance Variation with Temperature

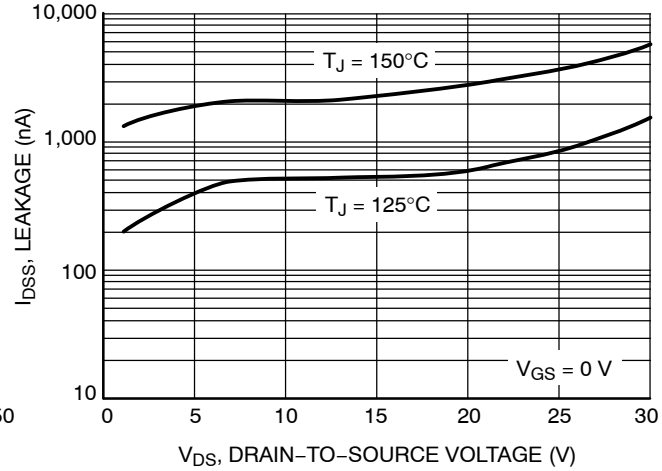


Figure 6. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS – Q1

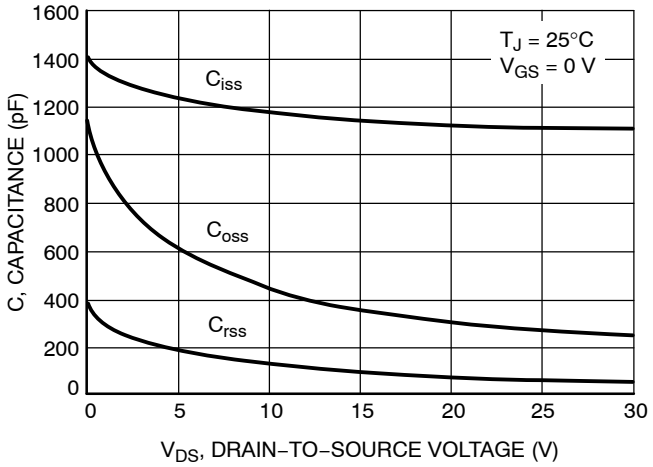


Figure 7. Capacitance Variation

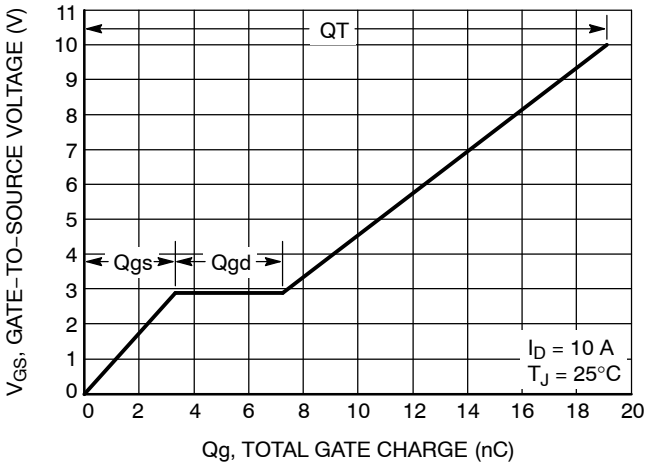


Figure 8. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

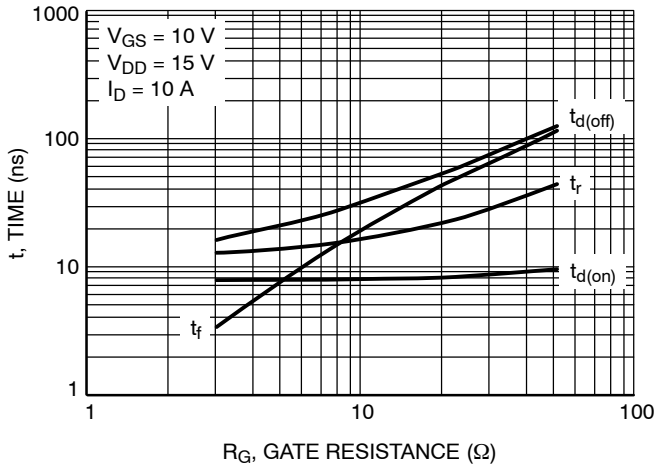


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

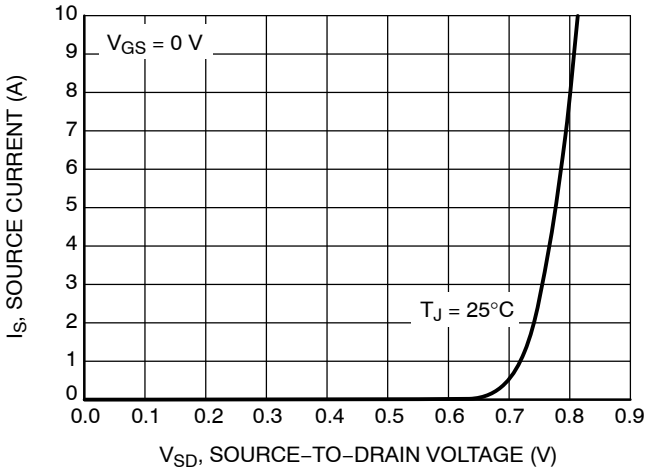


Figure 10. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS – Q2

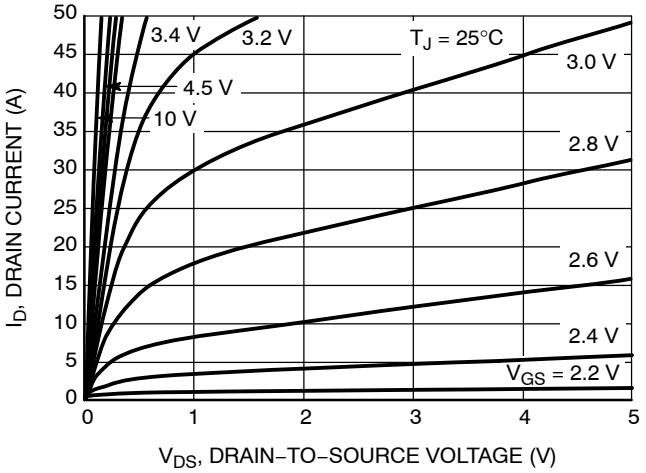


Figure 11. On−Region Characteristics

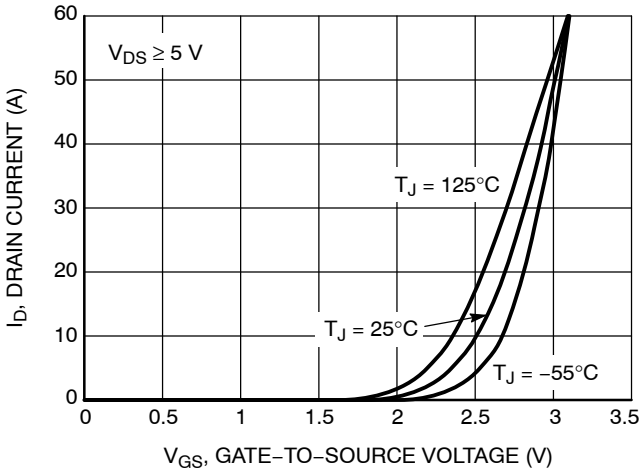


Figure 12. Transfer Characteristics

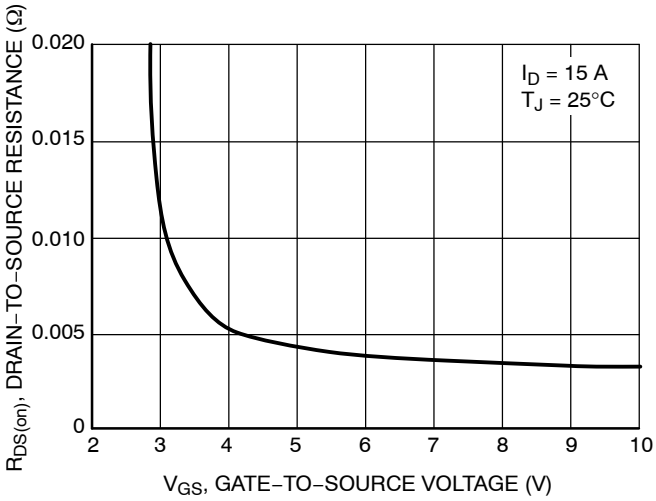


Figure 13. On−Resistance vs. Gate−to−Source Resistance

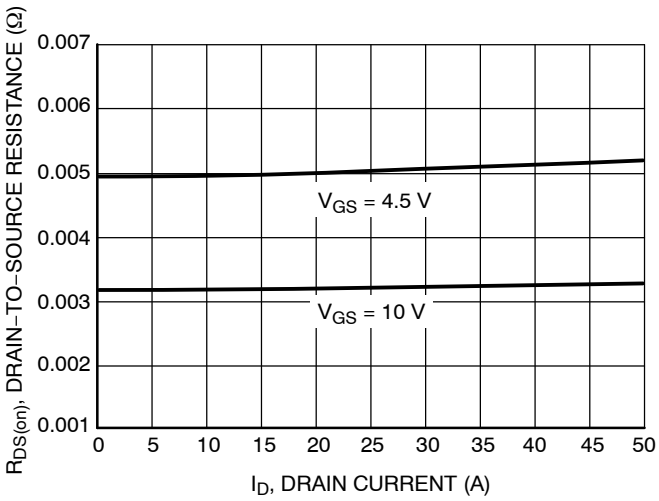


Figure 14. On−Resistance vs. Drain Current and Gate Voltage

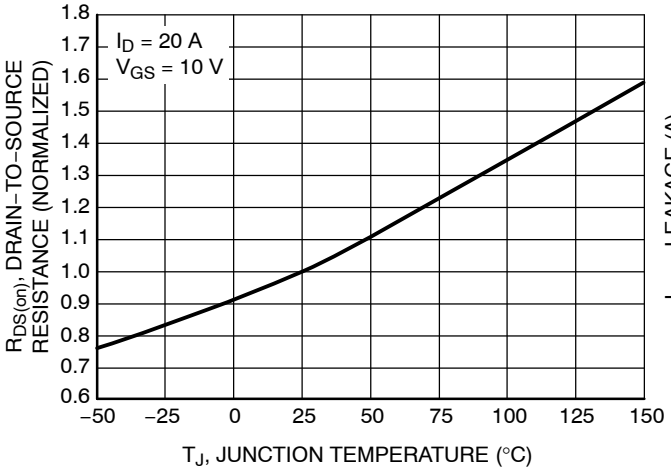


Figure 15. On−Resistance Variation with Temperature

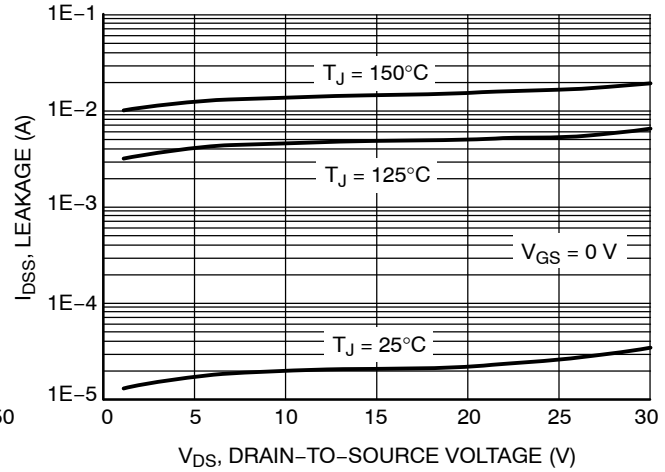


Figure 16. Drain−to−Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS – Q2

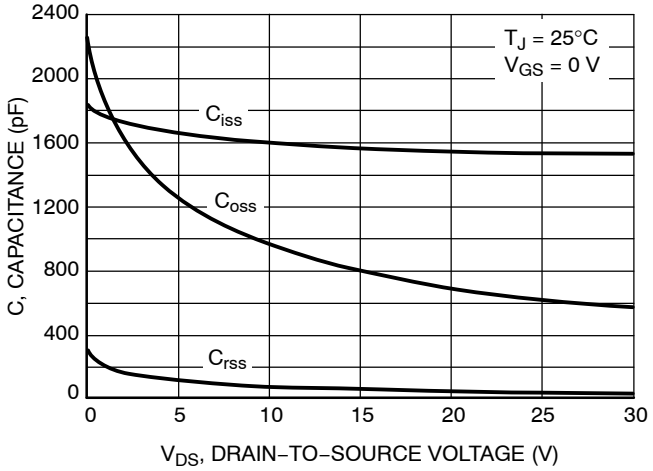


Figure 17. Capacitance Variation

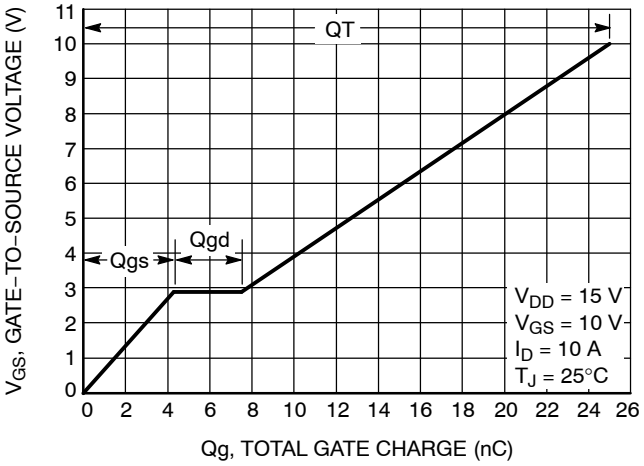


Figure 18. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

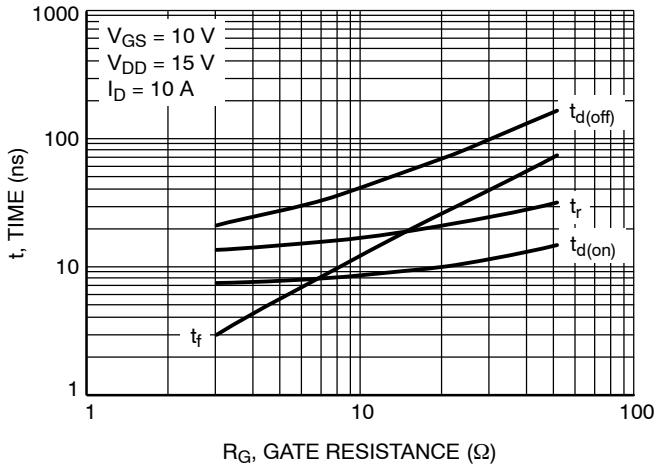


Figure 19. Resistive Switching Time Variation vs. Gate Resistance

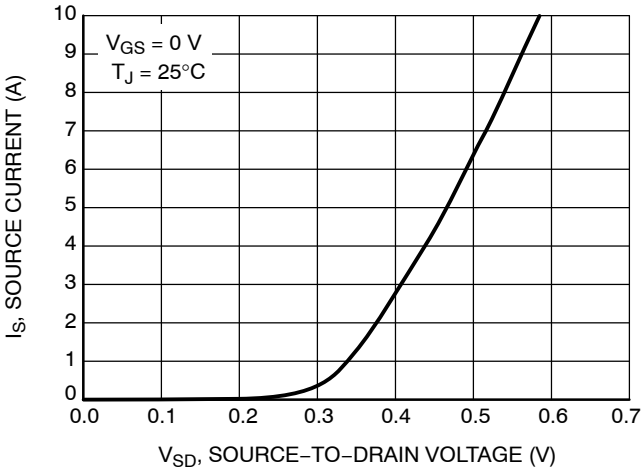
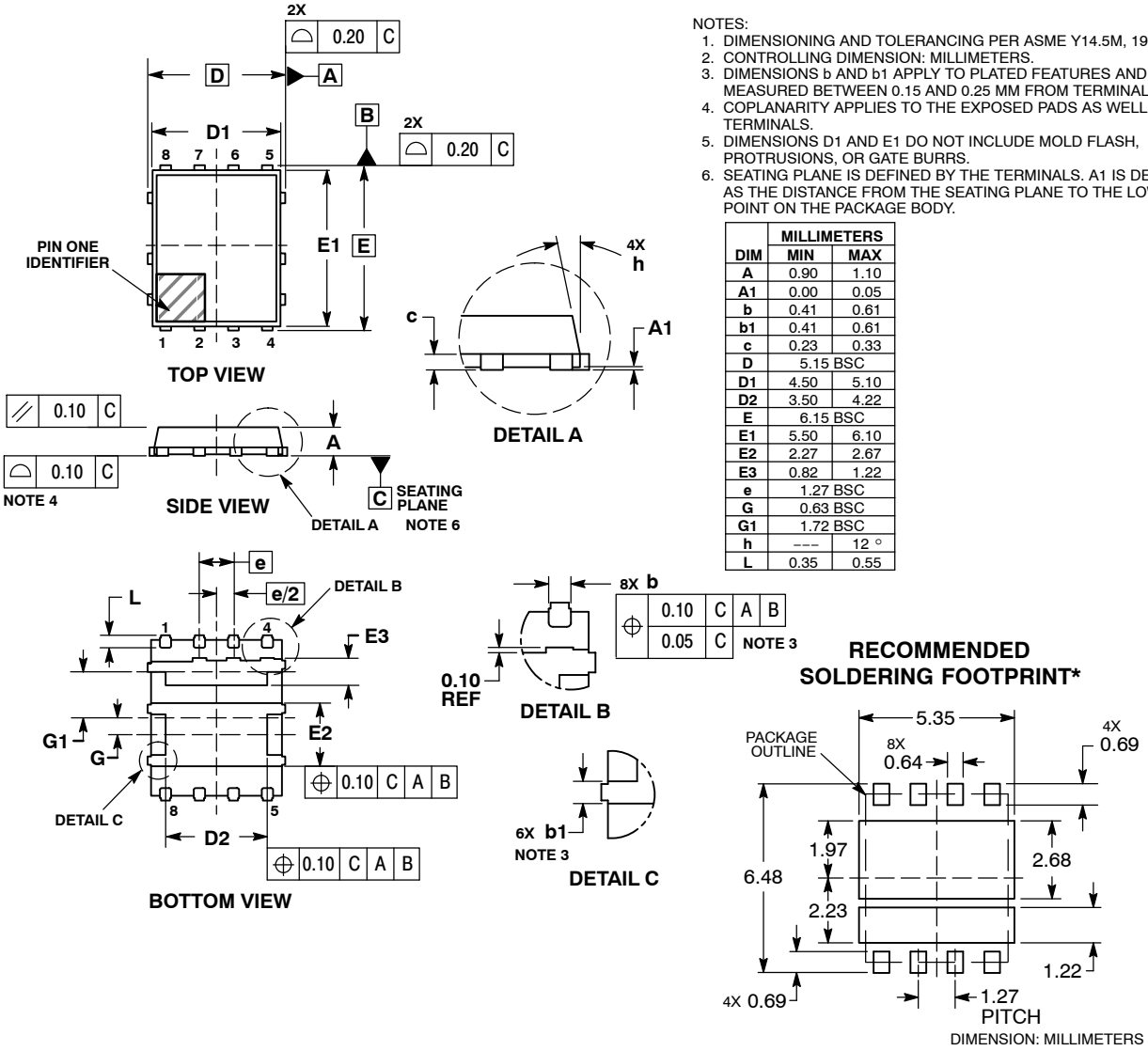


Figure 20. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

DFN8 5x6, 1.27P Dual Flag (SO8FL−Dual−Asymmetrical)
CASE 506BX
ISSUE C



NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSIONS b AND b1 APPLY TO PLATED FEATURES AND ARE MEASURED BETWEEN 0.15 AND 0.25 MM FROM TERMINAL TIPS.
4. COPLANARITY APPLIES TO THE EXPOSED PADS AS WELL AS THE TERMINALS.
5. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
6. SEATING PLANE IS DEFINED BY THE TERMINALS. A1 IS DEFINED AS THE DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT ON THE PACKAGE BODY.

	MILLIMETERS	
DIM	MIN	MAX
A	0.90	1.10
A1	0.00	0.05
b	0.41	0.61
b1	0.41	0.61
c	0.23	0.33
D	5.15 BSC	
D1	4.50	5.10
D2	3.50	4.22
E	6.15 BSC	
E1	5.50	6.10
E2	2.27	2.67
E3	0.82	1.22
e	1.27 BSC	
G	0.63 BSC	
G1	1.72 BSC	
h	---	12 °
L	0.35	0.55

RECOMMENDED SOLDERING FOOTPRINT*

DIMENSION: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

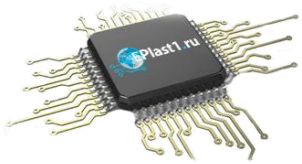
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)
Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.